



PT511B

TECHNICAL DATA

TO-Can PIN Photodiode

Ball Lens

PT511B is an InGaAs pin structure based photodiode on InP by MOCVD method and planar diffusing technology. The sensitive area is Ø 300µm respectively. TO-46 package with ball lens.



Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	U_R	1000	V
Reverse current	I_R	500	µA
Forward current	I_F	1000	mA
Power Dissipation	P_D	100	mW
Operating Temperature	T_{opr}	-40 ... +85	°C
Storage Temperature	T_{sta}	-40 ... +125	°C
Soldering Temperature (max. 10 s)	T_{sol}	260	°C

Specifications ($T_a=25^\circ\text{C}$)

Item	Value	Unit
Sensitive Area	Ø 300	µm
Spectral Response Range	Normal	Nm
	Broad	Nm
Responsivity (0 V)	$\lambda=850 \text{ nm}$	A/W
	$\lambda=1310 \text{ nm}$	A/W
	$\lambda=1550 \text{ nm}$	A/W
Linear Range (0 V)	-	-70 .. +10
	-	-55 .. +25
	-	-40 .. +30
Capacitance (-5 V)	≤ 12	pF
Dark Current (-5 V)	≤ 5	nA
Operating Voltage	0 .. -10	V
Linearity	-	dB
Splicing Deviation	± 0.1	Db
Splicing Life	10^5	Time
Highest Unsaturated Power	-	dBm



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Outline Dimensions

TO-46 (ball lens):

